

ABSTRACT OF THE DISCLOSURE

In the formation of a thin film on a substrate on which thin film transistors are formed with an electron beam evaporation method, there is provided a technique of forming a desired thin film without incurring abnormality in characteristics of the thin film transistor. The technique is characterized in that, in the formation of a thin film on an electrode, which is electrically connected with a thin film transistor, with an electron beam evaporation method, control of an acceleration voltage of electrons is performed such that, when an evaporation material for forming the thin film is irradiated with an electron beam, radial rays are not substantially radiated from the evaporation material. That the radial rays are not substantially radiated indicates that the control of an acceleration voltage of electrons is performed such that the thin film transistor is not deteriorated due to radial rays radiated from the evaporation material.